



# Bipolar NPN Bare Die – BTN6324

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## Part Description

The BTN6324 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. PNP Complement is BTP6324.

## Key Parameters:

- VCBO = 80V
- VCEO = 80V
- VEBO = 8V
- hFE = 56-390 @ VCE = 10V, IC = 0.15A
- VCE(Sat) = 0.4V @ IC = 0.5A, IB = 50mA
- fT = 230 MHz @ VCE = 10V, IE = 0A
- COBO = 15pF @ VCB = 10V

## Features

Low VCE(sat). Designed to provide performance equivalent to ROHM 2SC2061

## Die Size (Unawn)

700µm X 700µm, 28 Mils X 28 Mils

This is a shortform datasheet only

For the full datasheet

Please contact [sales@siliconsupplies.com](mailto:sales@siliconsupplies.com)

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